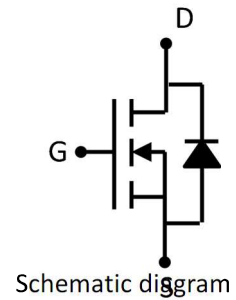


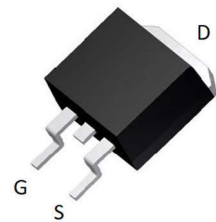
Feature

- 100V,145A
 $R_{DS(ON)} < 4.2m\Omega @ V_{GS}=10V$
- Advanced Trench Power MOSFET
- Provide Excellent $R_{DS(ON)}$ And Low Gate Charge



Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch
- Rectifier



TO-263 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
G042N01D	APG042N01D	TO-263		-	800

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_a = 25^\circ\text{C}$)	I_D	145	A
Continuous Drain Current ($T_a = 100^\circ\text{C}$)	I_D	105	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	380	A
Singel Pulsed Avalanche Energy ⁽²⁾	E_{AS}	660	mJ
Power Dissipation	P_D	215	W
Thermal Resistance from Junction to Case	$R_{\theta JC}$	0.44	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

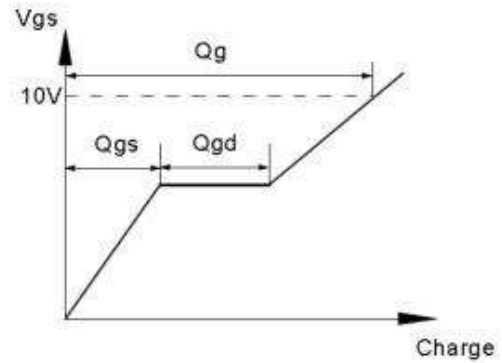
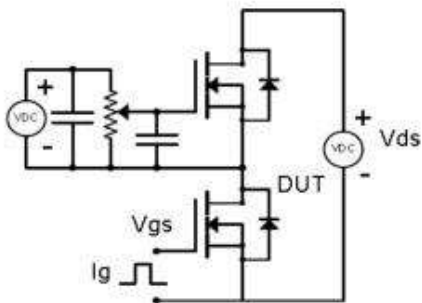
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	100	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =100V, V _{GS} = 0V	-	-	1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±20V, V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage ⁽³⁾	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	3	4	V
Drain-source on-resistance ⁽³⁾	R _{DS(on)}	V _{GS} =10V, I _D =70A	-	3.7	4.2	mΩ
Forward tranconductance ⁽³⁾	g _{FS}	V _{DS} =10V, I _D =70A	-	122	-	S
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f =1MHz	-	5678	-	pF
Output Capacitance	C _{oss}		-	673	-	
Reverse Transfer Capacitance	C _{rss}		-	27	-	
Switching characteristics						
Turn-on delay time	t _{d(on)}	V _{DD} =50V, I _D =70A, V _{GS} =10V, R _G =25Ω	-	25	-	ns
Turn-on rise time	t _r		-	33	-	
Turn-off delay time	t _{d(off)}		-	37	-	
Turn-off fall time	t _f		-	18	-	
Total Gate Charge	Q _g	V _{DS} =50V, I _D =70A, V _{GS} =10V	-	48.5	-	nC
Gate-Source Charge	Q _{gs}		-	2	-	
Gate-Drain Charge	Q _{gd}		-	32	-	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V _{DS}	V _{GS} =0V, I _S =140A	-	-	1.2	V
Diode Forward current ⁽⁴⁾	I _S		-	-	140	A
Reverse recovery time	T _{rr}	I _S =70A, V _{GS} =0V, dI _F /dt=100A/us		71		ns
Reverse recovery charge	Q _{rr}	I _S =70A, V _{GS} =0V, dI _F /dt=100A/us		144		nC

Notes:

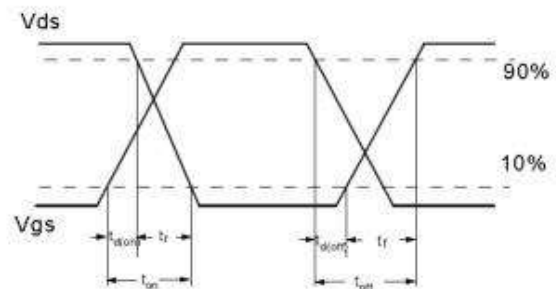
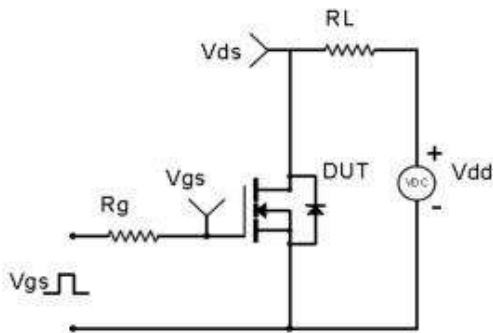
1. Repetitive Rating: pulse width limited by maximum junction temperature
2. EAS Condition: T_J=25°C, V_{DD}=50V, R_G=20 Ω, L=0.5mH
3. Pulse Test: pulse width≤300μs, duty cycle≤2%
4. Surface Mounted on FR4 Board, t≤10 sec

Test Circuit & Waveform

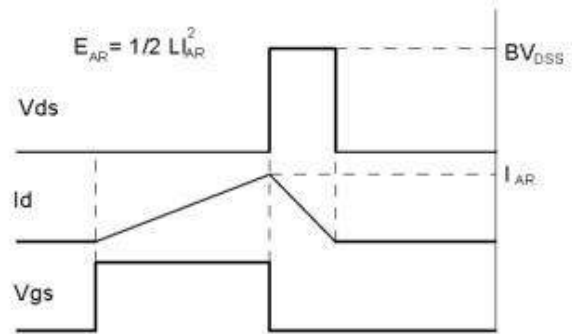
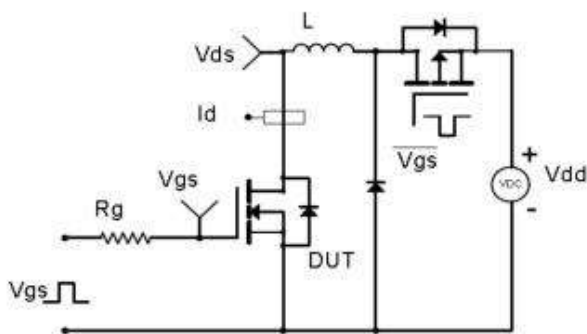
Gate Charge Test Circuit & Waveform



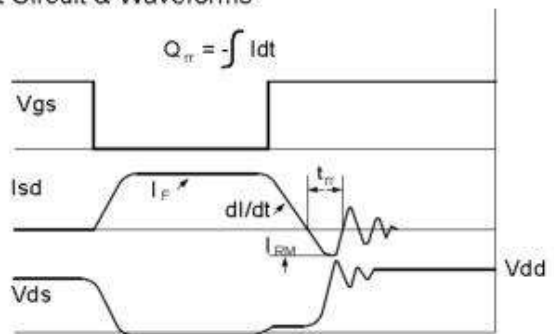
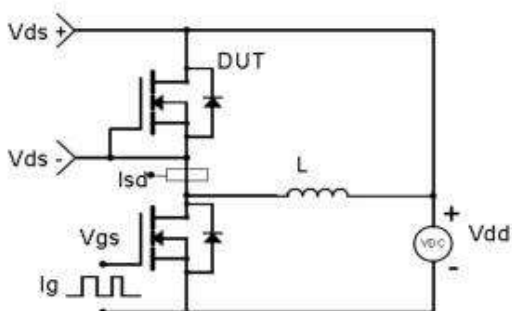
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Typical Electronic and Thermal Characteristics

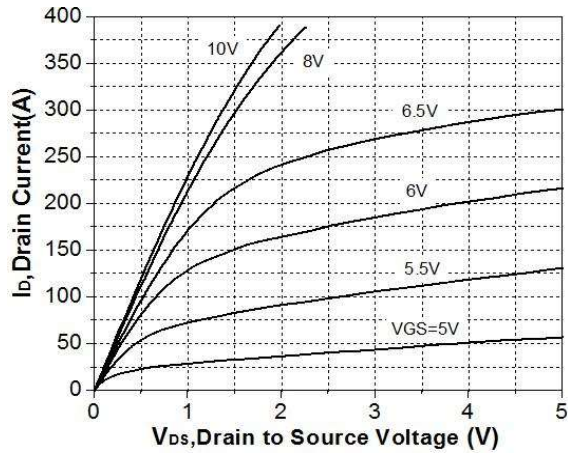


Figure 1. On-Region Characteristics

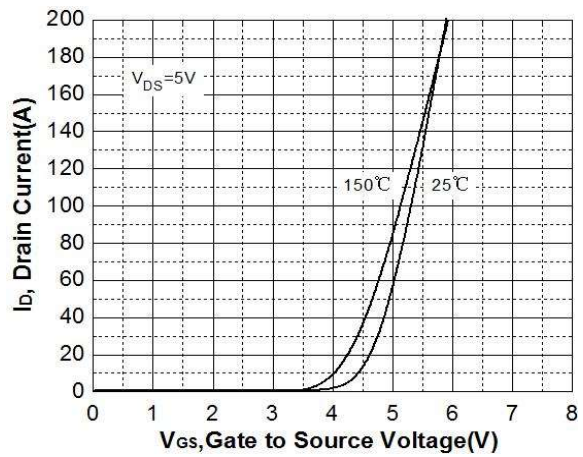


Figure 2. Transfer Characteristics

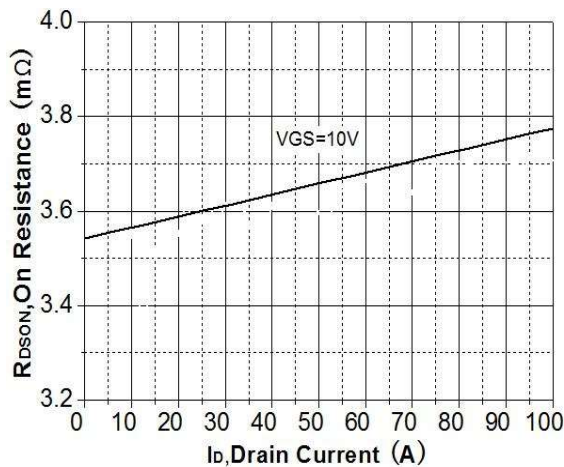


Figure 3. On-Resistance Variation vs Drain Current

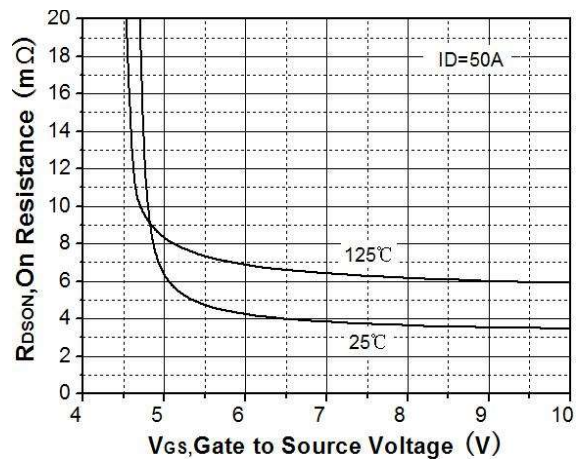


Figure 4. On-Resistance Vs Gate to Source Voltage

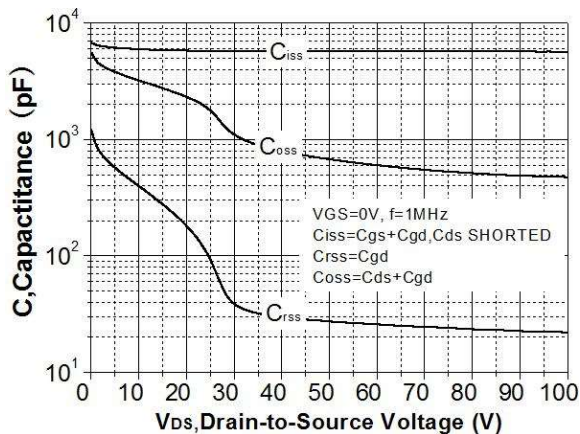


Figure 5. Capacitance Characteristics

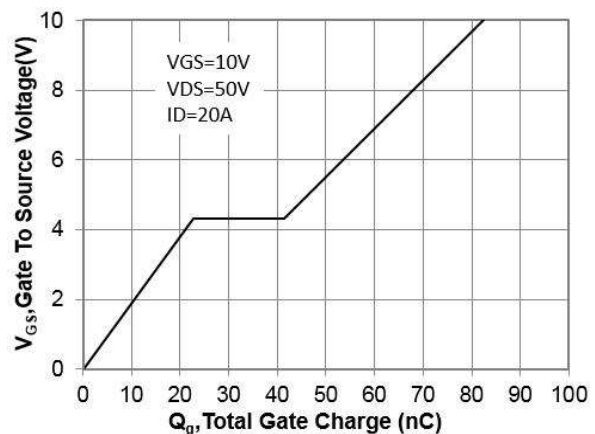


Figure 6. Gate Charge Characteristics

Typical Electronic and Thermal Characteristics

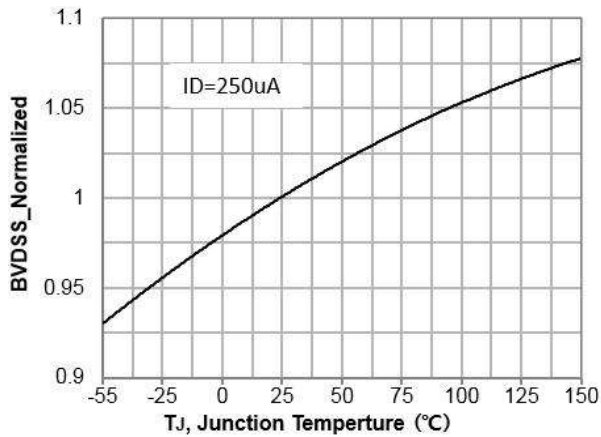


Figure 7. Breakdown Voltage Variation vs Temperature

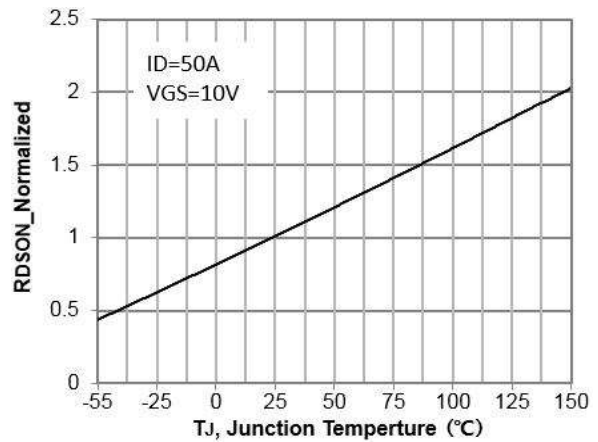


Figure 8. On-Resistance Variation vs Temperature

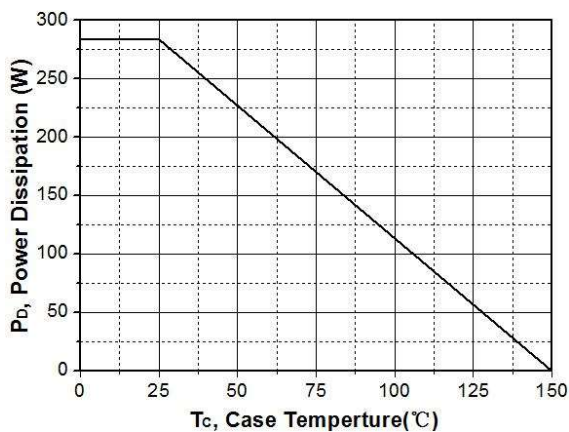


Figure 9. Power Dissipation

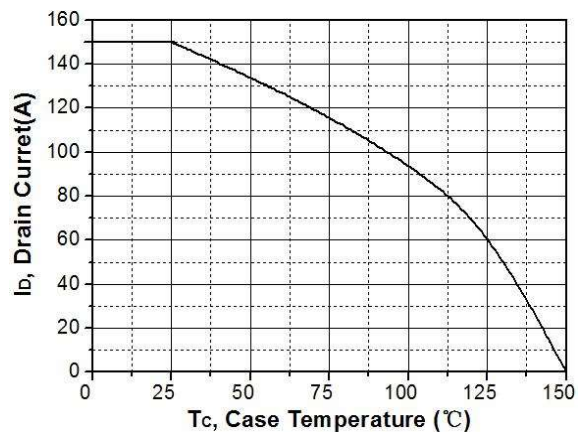


Figure 10. Drain Current Derating

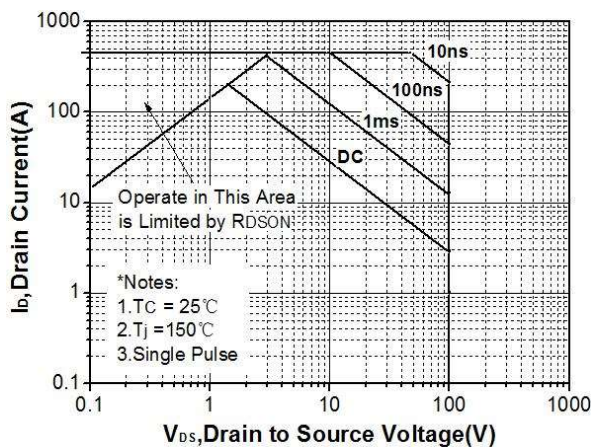


Figure 11. Maximum Safe Operating Area

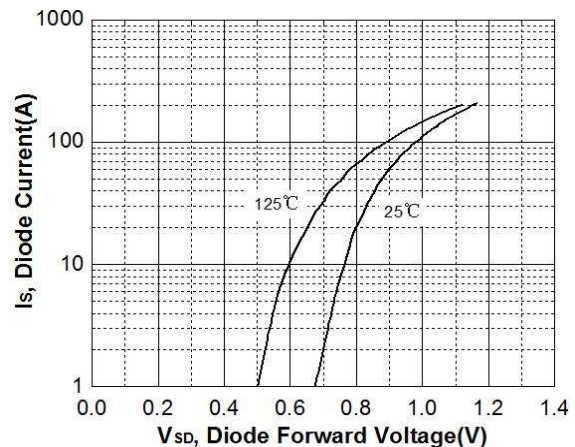
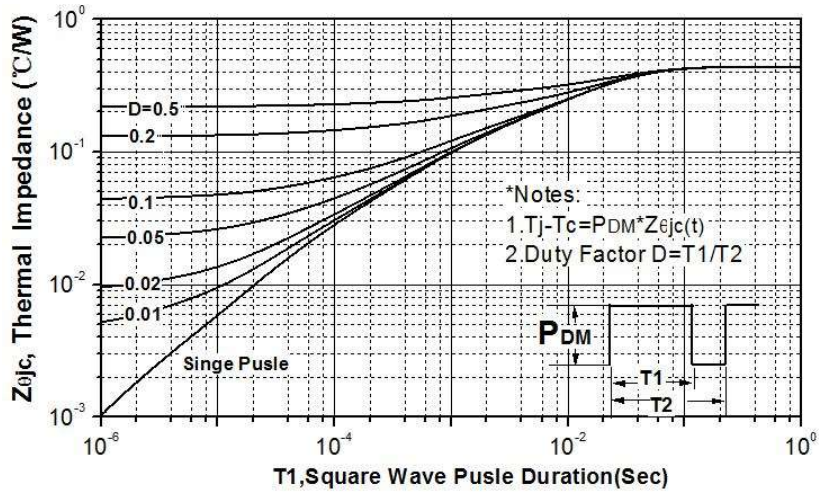
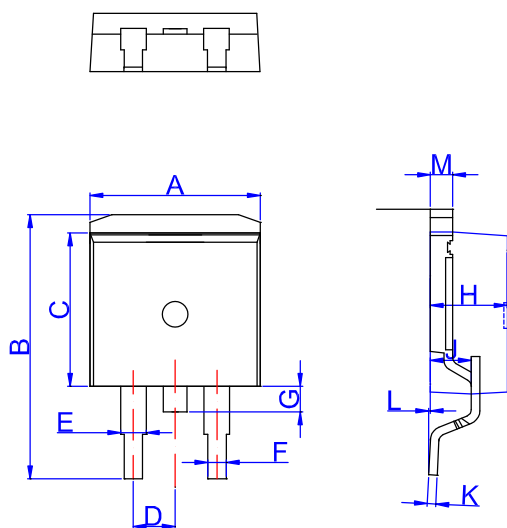


Figure 12. Body-diode Forward Characteristics

Typical Electronic and Thermal Characteristics



TO-263 Package Information



TO-263

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.4		9.6	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053

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[DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE2384](#) [DMC2700UDMQ-7](#) [DMN2080UCB4-7](#)
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[MCQ7328-TP](#) [SSM3J143TU,LXHF](#) [DMN12M3UCA6-7](#) [PJMF280N65E1_T0_00201](#) [PJMF380N65E1_T0_00201](#)
[PJMF280N60E1_T0_00201](#) [PJMF600N65E1_T0_00201](#) [PJMF900N65E1_T0_00201](#)